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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



2SC4546

Silicon NPN Triple Diffused Planar Transistor (High Voltage and Ultra-high Speed Switching Transistor) Application : Switching Regulator, Lighting Inverter and General Purpose

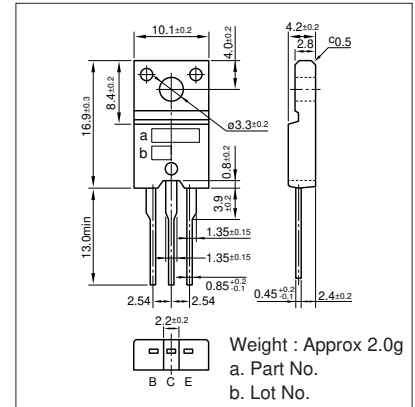
Absolute maximum ratings (Ta=25°C)

Symbol	Ratings	Unit
V _{CB0}	600	V
V _{CEO}	400	V
V _{EB0}	7	V
I _C	7(Pulse)14	A
I _B	2	A
P _C	30(T _C =25°C)	W
T _J	150	°C
T _{stg}	-55 to +150	°C

Electrical Characteristics (Ta=25°C)

Symbol	Conditions	Ratings	Unit
I _{CB0}	V _{CB} =600V	100max	μA
I _{EB0}	V _{EB} =7V	100max	μA
V _{(BR)CEO}	I _C =25mA	400min	V
h _{FE}	V _{CE} =4V, I _C =3A	10to25	
V _{CE(sat)}	I _C =3A, I _B =0.6A	0.7max	V
V _{BE(sat)}	I _C =3A, I _B =0.6A	1.3max	V
f _T	V _{CE} =12V, I _E =-0.5A	10typ	MHz
COB	V _{CB} =10V, f=1MHz	55typ	pF

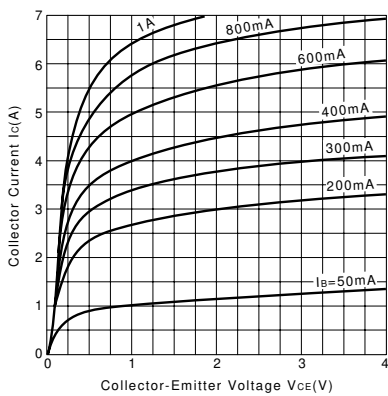
External Dimensions FM20(TO220F)



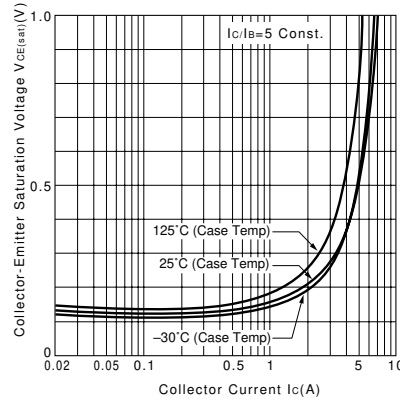
Typical Switching Characteristics (Common Emitter)

V _{CC} (V)	R _L (Ω)	I _C (A)	V _{BB1} (V)	V _{BB2} (V)	I _{B1} (A)	I _{B2} (A)	t _{on} (μs)	t _{stg} (μs)	t _f (μs)
200	67	3	10	-5	0.6	-1.2	0.5max	2max	0.15max

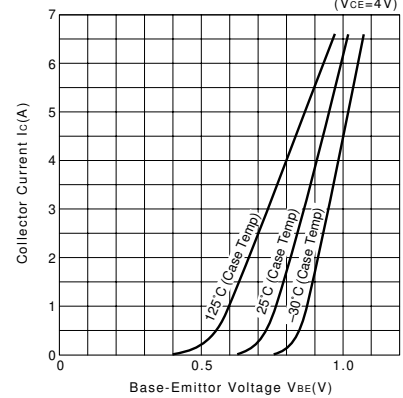
I_C-V_{CE} Characteristics (Typical)



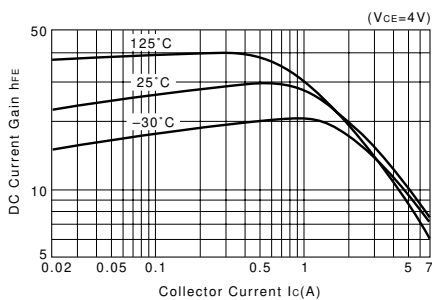
V_{CE(sat)}-I_C Characteristics (Typical)



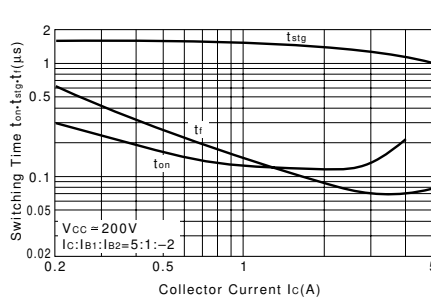
I_C-V_{BE} Temperature Characteristics (Typical)



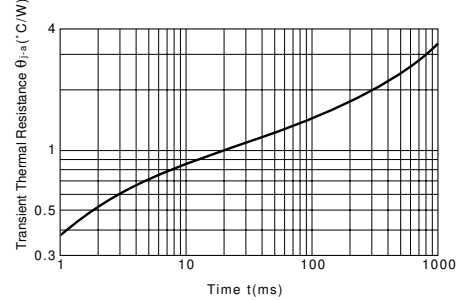
h_{FE}-I_C Temperature Characteristics (Typical)



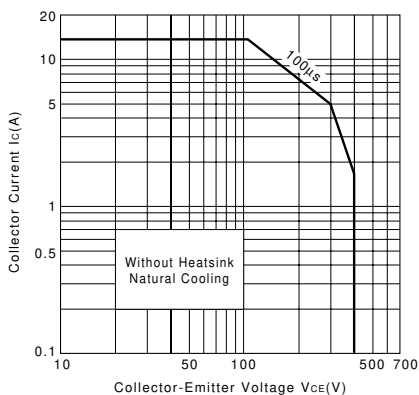
t_{on}•t_{stg}•t_f-I_C Characteristics (Typical)



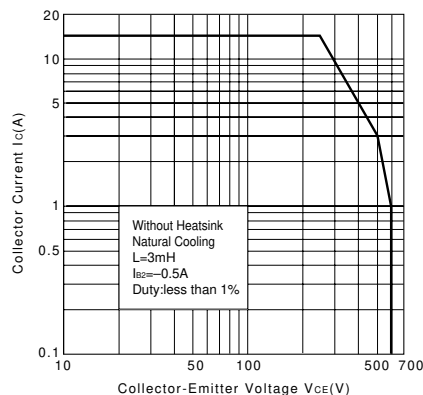
θ_{J-a}-t Characteristics



Safe Operating Area (Single Pulse)



Reverse Bias Safe Operating Area



P_C-T_a Derating

